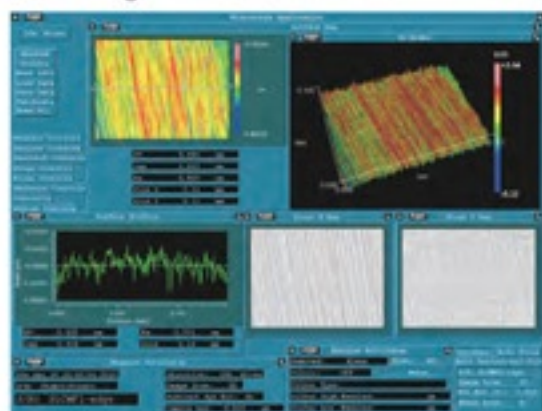


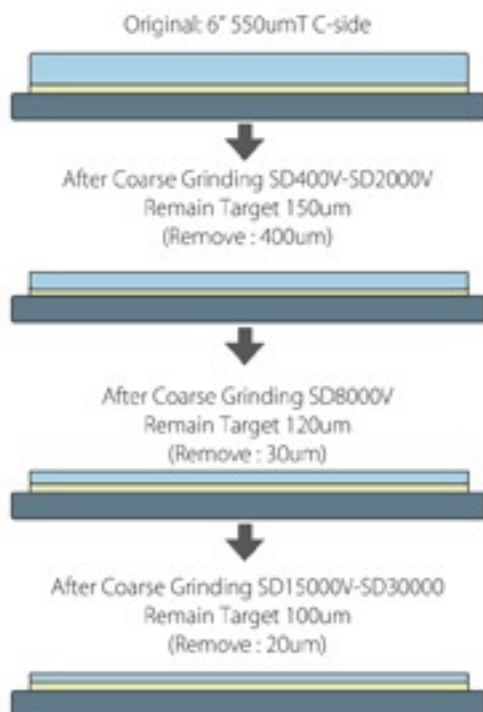
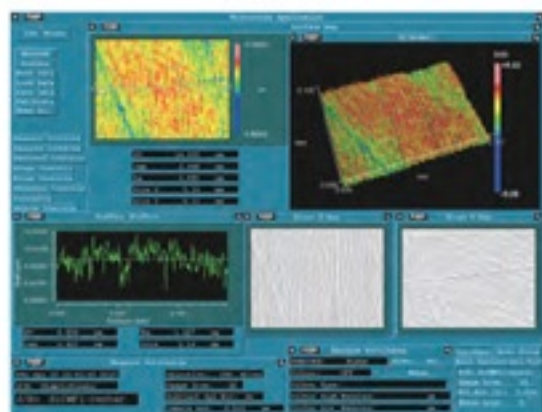
SiC WAFER

GRINDING PERFORMANCE

Wafer Edge VT#15000 Ra: 0.731nm

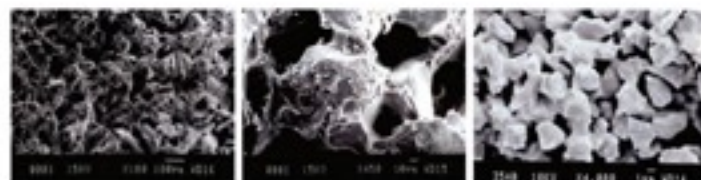


Wafer Center VT#15000 Ra: 1.127nm



VITRIFIED BOND

- Pores Bond Type / High grinding performance is realized.
- The bond hardness can be adjusted finely.
- Super high-speed processing for hard-to-cut materials is realized.



GENERAL PROCESSING CONDITION

Present Stage	
Wafer Size	3"
	4"
	6"
	C-side; Si-side
Target Thickness	50um
Feed Rate Process Time	#400: ~100um/min
	#2000: ~50um/min
	#8000: ~30um/min
	#15000: ~20um/min
	#30000: ~20um/min
Roughness	Ra ≤ 0.5~2nm
Wheel life	> 1000pcs